



### P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	Package	I <sub>D</sub> Max T <sub>A</sub> = +25°C
-20V	$52m\Omega @V_{GS} = -4.5V$	SOT23	-5.0A
-20V	$100 \text{m}\Omega @V_{GS} = -2.5 \text{V}$	30123	-3.6A

## **Description**

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$ , yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Backlighting
- Power Management Functions
- DC-DC Converters
- Motor Control

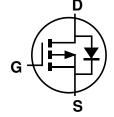
## **Features**

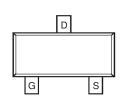
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMG2305UXQ</u>)

### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208 63
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)







Top View

Internal Schematic

Top View

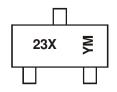
## **Ordering Information** (Note 4)

Part Number	Compliance	Case	Packaging
DMG2305UX-7	Standard	SOT23	3,000/Tape & Reel
DMG2305UX-13	Standard	SOT23	10.000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



 $23X = Product Type Marking Code YM = Date Code Marking Y or <math>\overline{Y} = Year (ex: F = 2018)$  M = Month (ex: 9 = September)

### Date Code Key

Year	2009	~	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026
Code	W	~	D	E	F	G	Н	ı	J	K	L	М	N
Mon	th	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



# **Maximum Ratings** $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		$V_{DSS}$	-20	V	
Gate-Source Voltage		$V_{GSS}$	±8	V	
Continuous Dusin Comment (Nets 5) V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		-4.2 -3.3	Α
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-5.0 -4.0	А
Pulsed Drain Current (10µs Pulse, Duty Cycle =	1%) (Note	I <sub>DM</sub>	-15	Α	

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Power Dissipation (Note 5)		$P_{D}$	1.4	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	В	90	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{ heta JA}$	64	°C/W
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	33	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

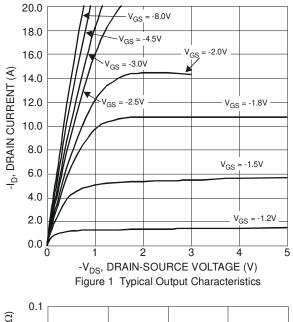
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

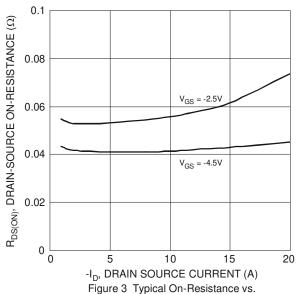
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current $T_J = +25$ °C	I <sub>DSS</sub>	_	_	-1.0	μΑ	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.5		-0.9	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	
			40	52		$V_{GS} = -4.5V$ , $I_D = -4.2A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	52	100	mΩ	$V_{GS} = -2.5V$ , $I_D = -3.4A$	
			68	200		$V_{GS} = -1.8V, I_D = -2A$	
Forward Transfer Admittance	Y <sub>FS</sub>	_	9	_	S	$V_{DS} = -5V, I_{D} = -4A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	$C_{iss}$	_	808	_	pF	V 45V V 0V	
Output Capacitance	Coss	_	85	_	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V -f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	77	_	рF	1 = 1.000112	
Gate Resistance	$R_g$		15.2		Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz$	
SWITCHING CHARACTERISTICS (Note 8)							
Total Gate Charge	$Q_g$	_	10.2	_	nC	V 4.5V.V 4V	
Gate-Source Charge	$Q_{gs}$	_	1.3	_	nC	$V_{GS} = -4.5V, V_{DS} = -4V,$ $I_{D} = -3.5A$	
Gate-Drain Charge	$Q_{gd}$	_	2.2	_	nC	ID = -3.5A	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	10.8	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	13.7	_	ns	$V_{DS} = -4V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	79.3	_	ns	$R_g = 6\Omega$ , $I_D = -1A$	
Turn-Off Fall Time	t <sub>F</sub>	_	34.7	_	ns		

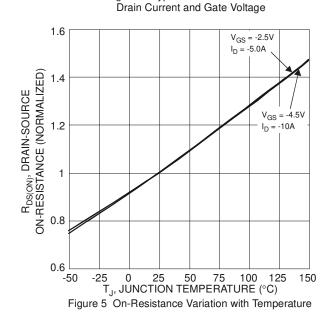
Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
- Repetitive rating, pulse width limited by junction temperature.
  Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.

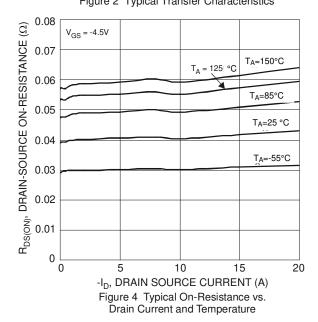


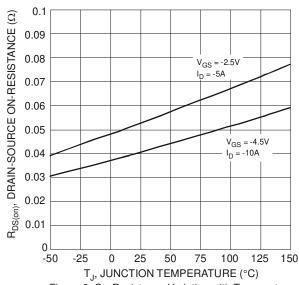






20 V<sub>DS</sub> = -5.0V T<sub>A</sub> = -55°C T<sub>A</sub> = 150°C T<sub>A</sub> = 150°C T<sub>A</sub> = 125°C T







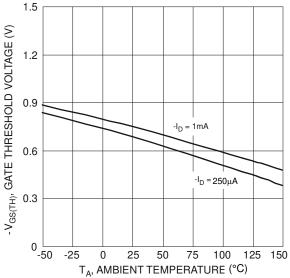
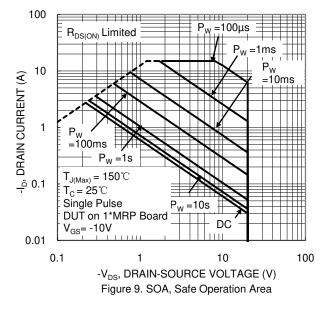
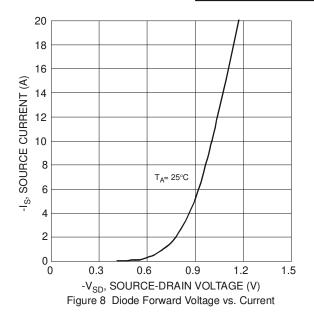


Figure 7 Gate Threshold Variation vs. Ambient Temperature



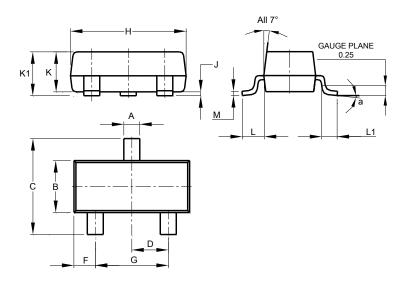




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23

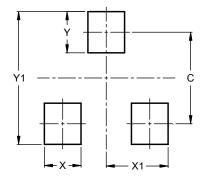


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
7	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
<b>a</b> 0°		8°	_				
All	All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23



Dimensions	Value (in mm)		
С	2.0		
X	0.8		
X1	1.35		
Υ	0.9		
Y1	2.9		



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